

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-2 (cancelled)

Claim 3 (currently amended): The method according to Claim 17, wherein the basic substance ~~The abrasive liquid for CMP process according to Claim 1, wherein said addition agent is fatty amine having a primary amino group, or and/or ammonia.~~

Claim 4 (currently amended): The method according to Claim 17, wherein the basic substance is included in the first abrasive liquid or the second abrasive liquid at an amount of 0.01 to 10 weight %. ~~The abrasive liquid for CMP process according to Claim 1, wherein a content of said addition agent is 0.01 weight % or more on a basis of a weight of the abrasive liquid.~~

Claim 5 (currently amended): The method according to Claim 17, ~~The abrasive liquid for CMP process according to Claim 1,~~ wherein said abrasive material is an inorganic substance of

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one kind or two kinds or more selected from a group consisting of silicon dioxide, aluminum oxide, cerium oxide, silicon nitride, and zirconium oxide.

Claim 6 (currently amended): The method according to Claim 17, The abrasive liquid for CMP process according to Claim 1, wherein said abrasive material is colloidal silica.

Claim 7 (cancelled)

Claim 8 (currently amended): The method of polishing according to Claim 17 ~~[[7]]~~, wherein a surface of said device wafer to be polished is formed of a film comprising at least silicon oxide.

Claims 9-10 (cancelled)

Claim 11 (currently amended): The method of polishing according to Claim 17 ~~[[7]]~~, wherein an abrasive pad with concentric recessing or spiral recessing is used.

Claim 12 (currently amended): The method of polishing according to Claim 17 ~~[[7]]~~, wherein pad conditioning is performed simultaneously with polishing for 10 % or more of polishing time.

Claim 13 (currently amended): The method of polishing according to Claim 17 ~~[[7]]~~, wherein, in dropping an abrasive liquid for CMP process into an abrasive pad, polishing is performed while putting an abrasive head on a side of a rotational direction of an abrasive table with respect to a dropping position of the abrasive liquid and putting the dropping position of the abrasive liquid on a side of a rotational direction of the abrasive table with respect to a pad conditioner and immediately near a center of the pad with respect to a center of the abrasive head.

Claim 14 (currently amended): A semiconductor device having a [[A]] layer insulation film or an element separation film obtained by polishing means of the method according to claim 17. ~~with a use of an abrasive liquid for CMP process according to claim 1.~~

Claim 15 (cancelled)

Claim 16 (currently amended): A magnetic head or a substrate for a liquid crystal display obtained by polishing means of the method according to claim 17. ~~with a use of an abrasive liquid for CMP process according to Claim 1.~~

Claim 17 (new): A method for polishing a device wafer by at least two stages, comprising:

a first stage of polishing the device wafer using a first abrasive liquid comprising a first abrasive material and a first aqueous solvent under a first polishing condition; and

a second stage of polishing the device wafer using a second abrasive liquid comprising a second abrasive material and a second aqueous solvent under a second polishing condition different from the first polishing condition;

wherein the first abrasive liquid or the second abrasive liquid further comprises a basic substance having a pKa of 7 to 11;

wherein the first abrasive material or the second abrasive material, including the basic substance, includes particles having a particle diameter of 20 to 80 nm at an amount of 15 to 80 weight % on a weight basis of the abrasive liquid;

wherein the second stage is performed under at least one of the following conditions:

- (1) that the first abrasive material is different from the second abrasive material;
- (2) that the second abrasive liquid has a dilution solution of the first abrasive liquid by 1.1 to 100 times;
- (3) that a ratio $[(r1)/(r2)]$ between a first average particle size (r1) of the first abrasive material and a second average particle size (r2) of the second abrasive material is 0.1 to 10.0;
- (4) that a pressure ratio $[(p1)/(p2)]$ between a first pressure (p1) applied on the device wafer in the first stage and a second pressure (p2) applied on the device wafer in the second stage is 0.3 to 5.0; and

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(5) that a rotational speed ratio $[(t1)/(t2)]$ between a first rotational speed (t1) applied in the first stage and a second rotational speed (t2) applied in the second stage is 0.2 to 2.0 a ratio.